

Koichi Murata

List of Publications by Year in descending order

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26
papers

1,123
citations

1040056

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642732

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all docs

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docs citations

26
times ranked

1962
citing authors

#	ARTICLE	IF	CITATIONS
1	Scale-Invariant Quantum Anomalous Hall Effect in Magnetic Topological Insulators beyond the Two-Dimensional Limit. <i>Physical Review Letters</i> , 2014, 113, 137201.	7.8	453
2	Electric-field control of spin-orbit torque in a magnetically doped topological insulator. <i>Nature Nanotechnology</i> , 2016, 11, 352-359.	31.5	212
3	Tailoring exchange couplings in magnetic topological-insulator/antiferromagnet heterostructures. <i>Nature Materials</i> , 2017, 16, 94-100.	27.5	137
4	Metal-to-insulator switching in quantum anomalous Hall states. <i>Nature Communications</i> , 2015, 6, 8474.	12.8	136
5	Enhancing electric-field control of ferromagnetism through nanoscale engineering of high-Tc Mn_xGe_{1-x} nanomesh. <i>Nature Communications</i> , 2016, 7, 12866.	12.8	35
6	Control of Spin-Wave Damping in YIG Using Spin Currents from Topological Insulators. <i>Physical Review Applied</i> , 2019, 11, .	3.8	30
7	Wide-ranging control of carrier lifetimes in n-type 4H-SiC epilayer by intentional vanadium doping. <i>Journal of Applied Physics</i> , 2019, 126, .	2.5	21
8	Analysis of carrier lifetimes in N-doped n-type 4H-SiC epilayers. <i>Journal of Applied Physics</i> , 2019, 126, .	2.5	15
9	Nanoengineering of an Si/MnGe quantum dot superlattice for high Curie-temperature ferromagnetism. <i>Nanoscale</i> , 2017, 9, 3086-3094.	5.6	13
10	Hybrid Laser Activation of Highly Concentrated Bi Donors in Wire-Doped Silicon. <i>Applied Physics Express</i> , 2010, 3, 061302.	2.4	9
11	Suppressed expansion of single Shockley stacking faults at narrow widths in 4H-SiC. <i>Applied Physics Express</i> , 2019, 12, 124002.	2.4	9
12	Evidence for ferromagnetic coupling at the doped topological insulator/ferrimagnetic insulator interface. <i>AIP Advances</i> , 2016, 6, 055813.	1.3	8
13	Time-resolved photoluminescence spectral analysis of phonon-assisted DAP and e-A recombination in N+B-doped n-type 4H-SiC epilayers. <i>Journal Physics D: Applied Physics</i> , 2019, 52, 10LT01.	2.8	7
14	Observation of carrier lifetime distribution in 4H-SiC thick epilayers using microscopic time-resolved free carrier absorption system. <i>Journal of Applied Physics</i> , 2020, 128, 105702.	2.5	7
15	Carrier lifetime control by intentional boron doping in aluminum doped p-type 4H-SiC epilayers. <i>Journal of Applied Physics</i> , 2021, 129, .	2.5	6
16	Mechanical-stressing measurements of formation energy of single Shockley stacking faults in 4H-SiC. <i>Applied Physics Express</i> , 2021, 14, 044001.	2.4	6
17	Atomic characterization of nano-facet nitridation at SiC (110) surface. <i>Applied Physics Letters</i> , 2018, 112, 131603.	3.3	4
18	Atomic layer doping of Mn magnetic impurities from surface chains at a Ge/Si hetero-interface. <i>Nanoscale</i> , 2018, 10, 295-301.	5.6	4

#	ARTICLE	IF	CITATIONS
19	Dopant activation mechanism of Bi wire- δ -doping into Si crystal, investigated with wavelength dispersive fluorescence x-ray absorption fine structure and density functional theory. Journal of Physics Condensed Matter, 2017, 29, 155001.	1.8	3
20	Limited current conduction due to various types of stacking faults in n-type 4H-SiC epilayers. Applied Physics Express, 2022, 15, 045502.	2.4	3
21	Suppression of Bipolar Degradation in 4H-SiC Power Devices by Carrier Lifetime Control. , 2019, , .		2
22	Autosurfactant of the second kind: Bi enables δ -doping of Bi in Si. Applied Physics Letters, 2017, 111, 152104.	3.3	1
23	Fabrication of 4H-SiC PiN diodes on substrate grown by HTCVD method. Japanese Journal of Applied Physics, 2020, 59, SGGD07.	1.5	1
24	Direct nitridation of 4H-SiC(0001) surface by H ₂ /N ₂ treatment. Applied Physics Express, 2020, 13, 095506.	2.4	1
25	Peak Effect as Precursor to Lock-in State in Bi ₂ Sr ₂ CaCu ₂ O ₈ + δ Single Crystal. AIP Conference Proceedings, 2006, , .	0.4	0
26	Activation of two dopants, Bi and Er in δ -doped layer in Si crystal. Nano Futures, 2021, 5, 045005.	2.2	0